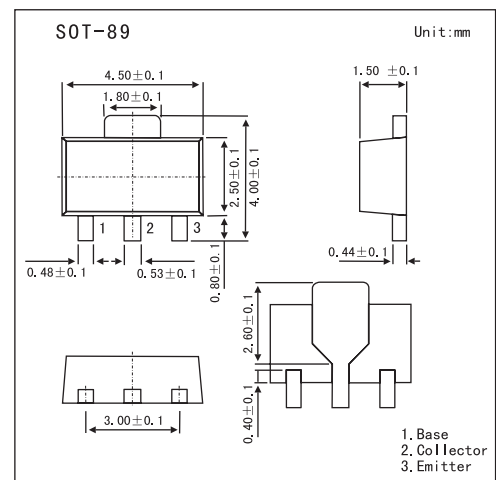


Medium Power Transistor

2SD2391

■ Features

- Low saturation voltage.
- Collector-emitter voltage =60V.
- PC=2 W (on 40×40×0.7mm ceramic board).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	60	V
Collector-emitter voltage	V _{CEO}	60	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	2	A
Collector power dissipation	P _C	0.5	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _C =50μA	60			V
Collector-emitter breakdown voltage	BV _{CEO}	I _C =1mA	60			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =50μA	6			V
Collector cutoff current	I _{CBO}	V _{CB} =50V			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} =5V			0.1	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A, I _B =50mA		0.13	0.35	V
DC current transfer ratio	h _{FE}	V _{CE} =-2V, I _C =-0.5A	120		270	
Output capacitance	f _T	V _{CE} =2V, I _E =-0.5A, f=100MHz		210		MHz
Transition frequency	C _{ob}	V _{CB} =10V, I _E =0A, f=1MHz		21		pF

■ Marking

Marking	DTQ
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